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Electron Devices, IEEE Transactions on , Volume: 48 Issue: 7 , July 2001

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Sun-Jay Chang; Chun-Yen Chang; Coming Chen; Jih-Wen Chou; Tien-Sheng Tiao-Yuan Huang

IEEE Electron Device Letters , Volume: 21 Issue: 9 , Sept. 2000

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IEEE Electron Device Letters , Volume: 21 Issue: 3 , March 2000

Page(s): 127 -129

[\[Abstract\]](#) [\[PDF Full-Text \(64 KB\)\]](#) **JNL****4 high-performance and high-reliability 80-nm gate-length DT MOS with indium super steep retrograde channel***Sun-Jay Chang; Chun-Yen Chang; Coming Chen; Tien-Sheng Chao; Yao-Jen*

Tiao-Yuan Huang

Electron Devices, IEEE Transactions on , Volume: 47 Issue: 12 , Dec. 2000
Page(s): 2379 -2384

[\[Abstract\]](#) [\[PDF Full-Text \(168 KB\)\]](#) **JNL**

**5 A 1.5 V high performance mixed signal integration with indium cha
130 nm technology node**

*Morifuji, E.; Oishi, A.; Miyashita, K.; Aota, S.; Nishigori, M.; Ootani, H.; Nak.
Miyamoto, K.; Matsuoka, F.; Noguchi, T.; Kakumu, M.*

Electron Devices Meeting, 2000. IEDM Technical Digest. International , 2000
Page(s): 459 -462

[\[Abstract\]](#) [\[PDF Full-Text \(280 KB\)\]](#) **CNF**

**6 High energy, high current performance of the GSD/VHE implanter
production of high dose p-type buried layers**

Namaroff, M.; Merrill, J.

Ion Implantation Technology, 2000. Conference on , 2000
Page(s): 411 -414

[\[Abstract\]](#) [\[PDF Full-Text \(332 KB\)\]](#) **CNF**

**7 Technical and economic considerations for retrograde well and cha
implants**

Morris, W.; Rubin, L.

Ion Implantation Technology, 2000. Conference on , 2000
Page(s): 73 -76

[\[Abstract\]](#) [\[PDF Full-Text \(312 KB\)\]](#) **CNF**

**8 Recognition of antegrade and retrograde atrial activation patterns
hybrid wavelet neural network schemes**

Strauss, D.; Jung, J.; Rieder, A.

Computers in Cardiology 2000 , 2000
Page(s): 545 -548

[\[Abstract\]](#) [\[PDF Full-Text \(340 KB\)\]](#) **CNF**

9 Design of sub-100 nm CMOSFETs: gate dielectrics and channel eng

*Seungheon Song; Kim, W.S.; Lee, J.S.; Choe, T.H.; Choi, J.H.; Kang, M.S.;
U.I.; Lee, N.I.; Fujihara, K.; Kang, H.K.; Lee, S.I.; Lee, M.Y.*

VLSI Technology, 2000. Digest of Technical Papers. 2000 Symposium on , 20
Page(s): 190 -191

[\[Abstract\]](#) [\[PDF Full-Text \(228 KB\)\]](#) **CNF**

10 Effects of nitrogen on the activation/deactivation of boron and in n-channel CMOS devices

Aronowitz, S.; Puchner, H.; Zubcov, V.

Simulation of Semiconductor Processes and Devices, 2000. SISPAD 2000. 20 International Conference on , 2000

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[\[Abstract\]](#) [\[PDF Full-Text \(280 KB\)\]](#) **CNF**

11 Study of quarter-micrometre retrograde well: device characteristics against temperature

Swe Toe-Naing; Yeo Kiat-Seng

Electronics Letters , Volume: 35 Issue: 4 , 18 Feb. 1999

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[\[Abstract\]](#) [\[PDF Full-Text \(204 KB\)\]](#) **JNL**

12 The effect of deterministic spatial variations in retrograde well in shallow trench isolation for sub-0.18 μm CMOS technology

Kapila, D.; Jain, A.; Nandakumar, M.; Ashburn, S.; Vasanth, K.; Sridhar, S.

Semiconductor Manufacturing, IEEE Transactions on , Volume: 12 Issue: 4 ,

Page(s): 457 -461

[\[Abstract\]](#) [\[PDF Full-Text \(124 KB\)\]](#) **JNL**

13 Optimization of V_{th} roll-off in MOSFET's with advanced channel architecture-retrograde doping and pockets

Gwoziecki, R.; Skotnicki, T.; Bouillon, P.; Gentil, P.

Electron Devices, IEEE Transactions on , Volume: 46 Issue: 7 , July 1999

Page(s): 1551 -1561

[\[Abstract\]](#) [\[PDF Full-Text \(332 KB\)\]](#) **JNL**

14 LOCOS vs. shallow trench isolation latch-up using MeV implantation well formation down to 0.18 μm design rules

Borland, J.O.; Cho, H.T.; Kim, J.K.

Ion Implantation Technology Proceedings, 1998 International Conference on 1 , 1998

Page(s): 67 -70 vol.1

[\[Abstract\]](#) [\[PDF Full-Text \(308 KB\)\]](#) **CNF**

15 Beam tuning with continuously variable aperture

Murakami, T.; Sugitani, M.; Tsukihara, M.; Sogabe, H.

Ion Implantation Technology Proceedings, 1998 International Conference on
1, 1998

Page(s): 428 -431 vol.1

[\[Abstract\]](#) [\[PDF Full-Text \(312 KB\)\]](#) **CNF**

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Ion Implantation Technology Proceedings, 1998 International Conference on 1, 1998

Page(s): 358 -361 vol.1

[\[Abstract\]](#) [\[PDF Full-Text \(252 KB\)\]](#) **CNF****17 50 nm gate-length CMOS transistor with super-halo: design, process, and reliability***Bin Yu; Haihong Wang; Milic, O.; Qi Xiang; Weizhong Wang; An, J.X.; Ming-Electron Devices Meeting, 1999. IEDM Technical Digest. International, 1999*

Page(s): 653 -656

[\[Abstract\]](#) [\[PDF Full-Text \(292 KB\)\]](#) **CNF****18 Performance trade-offs of argon implanted SOI MOSFETs with In retrograde channel doping***Xu, X.-L.; Widenhofer, R.; Yu, Y.; Zia, O.; Pozder, S.; Hall, D.; Rashed, M.; Jallepalli, S.; Connelly, D.; Van Gompel, T.; Olivares, M.; Mendicino, M.; Car J.; Veeraraghavan, S.; Dow, D.*

SOI Conference, 1999. Proceedings. 1999 IEEE International, 1999

Page(s): 90 -91

[\[Abstract\]](#) [\[PDF Full-Text \(116 KB\)\]](#) **CNF****19 High performance 0.18 um nMOSFET by TED suppression**

Hyun-Sik Kim; Jong-Hyon Ahn; Duk-Min Lee; Soo-Cheol Lee; Kwang-Pyuk S
VLSI and CAD, 1999. ICVC '99. 6th International Conference on , 1999
Page(s): 140 -142

[\[Abstract\]](#) [\[PDF Full-Text \(192 KB\)\]](#) [CNF](#)

20 Channel formation for 0.15 /spl mu/m CMOS using through-the-g implantation

Montree, A.H.; Ponomarev, Y.V.; Baks, W.M.; van Brandenburg, A.C.M.C.; L
Roes, S.F.M.; Schmitz, J.; Stolk, P.A.; Tuinhout, H.P.

VLSI Technology, Systems, and Applications, 1999. International Symposiur
1999

Page(s): 10 -13

[\[Abstract\]](#) [\[PDF Full-Text \(256 KB\)\]](#) [CNF](#)

**21 MeV implantation introduced damage at the LOCOS bird's beak in
mu/m flash memory devices**

Wu, H.J.; Bhattacharya, S.; Krishnamurthy, S.; Sharma, U.

Ion Implantation Technology Proceedings, 1998 International Conference on
2 , 1998

Page(s): 937 -938 vol.2

[\[Abstract\]](#) [\[PDF Full-Text \(204 KB\)\]](#) [CNF](#)

**22 A study on the defects in the fabrication of CMOS retrograde well
a buried layer using MeV ion implantation**

Yoon-Taek Jang; Tae-Hoon Huh; Jae-Sang Ro

Ion Implantation Technology Proceedings, 1998 International Conference on
2 , 1998

Page(s): 959 -962 vol.2

[\[Abstract\]](#) [\[PDF Full-Text \(544 KB\)\]](#) [CNF](#)

**23 The effect of deterministic spatial variations in retrograde well im
shallow trench isolation and latchup immunity**

Kapila, D.; Jain, A.; Nandakumar, M.; Ashburn, S.; Vasanth, K.; Sridhar, S.

Statistical Metrology, 1998. 3rd International Workshop on , 1998

Page(s): 72 -75

[\[Abstract\]](#) [\[PDF Full-Text \(196 KB\)\]](#) [CNF](#)

**24 Channel profile engineering of 0.1 /spl mu/m-Si MOSFETs by
through-the-gate implantation**

Ponomarev, Y.V.; Stolk, P.A.; van Brandenburg, A.C.M.C.; Roes, R.; Montreuil Schmitz, J.; Woerlee, P.H.

Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International , :
Page(s): 635 -638

[\[Abstract\]](#) [\[PDF Full-Text \(300 KB\)\]](#) **CNF**

25 Shallow trench isolation for advanced ULSI CMOS technologies

Nandakumar, M.; Chatterjee, A.; Sridhar, S.; Joyner, K.; Rodder, M.; Chen, N.
Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International , :
Page(s): 133 -136

[\[Abstract\]](#) [\[PDF Full-Text \(564 KB\)\]](#) **CNF**

26 Impact of channel doping and Ar implant on device characteristics of partially depleted SOI MOSFETs

Xu, X.; Widenhofer, R.; Rashed, M.; Jallepalli, S.; Thorn, J.; Mendicino, M.; Candelaria, J.
SOI Conference, 1998. Proceedings., 1998 IEEE International , 1998
Page(s): 115 -116

[\[Abstract\]](#) [\[PDF Full-Text \(204 KB\)\]](#) **CNF**

27 Recognition of ventricular tachycardia with 1:1 retrograde atrial A new algorithm for implantable cardioverter defibrillators

Thompson, J.; Jenkins, J.
Engineering in Medicine and Biology Society, 1997. Proceedings of the 19th International Conference of the IEEE , Volume: 1 , 1997
Page(s): 393 -394 vol.1

[\[Abstract\]](#) [\[PDF Full-Text \(200 KB\)\]](#) **CNF**

28 Comparison of latchup immunity for silicided source/drain at different implant energy

Leong Kam Chew; Liu Po Chen; Gan Chock Hing; Qian Gang; Lee Yong Meng Chan
Electron Devices Meeting, 1997. Proceedings., 1997 IEEE Hong Kong , 1997
Page(s): 15 -18

[\[Abstract\]](#) [\[PDF Full-Text \(244 KB\)\]](#) **CNF**

29 Latchup characterization of high energy ion implanted new CMOS wells that comprised the BILLI (buried implanted layer for lateral iso and BL/CL (buried layer/connecting layer) structures

Jong-Kwan Kim; Seong-Hyung Park; Young-Jong Lee; Yung-Kwon Sung
Reliability Physics Symposium, 1997. 35th Annual Proceedings., IEEE Intern
1997
Page(s): 346 -352

[\[Abstract\]](#) [\[PDF Full-Text \(448 KB\)\]](#) [CNF](#)

**30' Effects of channel and source/drain implants on partially-depleted
MOSFETs**

Cao, M.; Vande Voorde, P.; Diaz, C.; Greene, W.

SOI Conference, 1996. Proceedings., 1996 IEEE International , 1996
Page(s): 98 -99

[\[Abstract\]](#) [\[PDF Full-Text \(196 KB\)\]](#) [CNF](#)

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Ion Implantation Technology. Proceedings of the 11th International Conferer 1997

Page(s): 661 -664

[\[Abstract\]](#) [\[PDF Full-Text \(384 KB\)\]](#) **CNF****32 Suppression of ion-induced charge collection against soft-error***Kishimoto, T.; Takai, N.; Ohno, Y.; Sayama, H.; Nishimura, T.*

Ion Implantation Technology. Proceedings of the 11th International Conferer 1997

Page(s): 9 -12

[\[Abstract\]](#) [\[PDF Full-Text \(412 KB\)\]](#) **CNF****33 Buried layer/connecting layer high energy implantation for impro latch-up***Morris, W.; Rubin, L.; Wristers, D.*

Ion Implantation Technology. Proceedings of the 11th International Conferer 1997

Page(s): 796 -799

[\[Abstract\]](#) [\[PDF Full-Text \(300 KB\)\]](#) **CNF****34 Epi avoidance for CMOS logic devices using MeV implantation***Borland, J.O.; Wristers, D.; Walker, J.*

Ion Implantation Technology. Proceedings of the 11th International Conference
1997
Page(s): 21 -24

[\[Abstract\]](#) [\[PDF Full-Text \(300 KB\)\]](#) [CNF](#)

35 Energy contamination from multiple-charged ion implantation in conventional implanter

Kubo, T.; Hisaeda, T.; Miyake, T.; Ishigaki, T.; Kase, M.; Watanabe, K.; Fuk
Ion Implantation Technology. Proceedings of the 11th International Conference
1997
Page(s): 100 -103

[\[Abstract\]](#) [\[PDF Full-Text \(248 KB\)\]](#) [CNF](#)

36 End station and beam line design considerations for photoresist on with high energy (MeV) ion implantation

O'Connor, J.P.; Tokoro, N.
Ion Implantation Technology. Proceedings of the 11th International Conference
1997
Page(s): 350 -354

[\[Abstract\]](#) [\[PDF Full-Text \(384 KB\)\]](#) [CNF](#)

37 Degradation of MOSFETs drive current due to halo ion implantation

Hyunsang Hwang; Dong-Hoon Lee; Jeong Mo Hwang
Electron Devices Meeting, 1996., International , 1996
Page(s): 567 -570

[\[Abstract\]](#) [\[PDF Full-Text \(320 KB\)\]](#) [CNF](#)

38 MeV implants boost device design

Voldman, S.H.
IEEE Circuits and Devices Magazine , Volume: 11 Issue: 6 , Nov. 1995
Page(s): 8 -16

[\[Abstract\]](#) [\[PDF Full-Text \(700 KB\)\]](#) [JNL](#)

39 A high performance deep submicron MOSFET structure with self-aligned selectively grown W-gate (SAW)

Yo Hwan Koh; Chan Kwang Park; Seong Min Hwang; Kwang Myoung Rho; M Chung; Dai-Hoon Lee
VLSI Technology, Systems, and Applications, 1995. Proceedings of Technical
1995 International Symposium on , 1995

Page(s): 268 -272

[\[Abstract\]](#) [\[PDF Full-Text \(252 KB\)\]](#) [CNF](#)

40 The effect of hydrogen denudation on thin oxides, device performance and epitaxial elimination

Fulford, J.; Wristers, D.; Gardner, M.

University/Government/Industry Microelectronics Symposium, 1995., Proceedings of the Eleventh Biennial, 1995

Page(s): 85 -89

[\[Abstract\]](#) [\[PDF Full-Text \(468 KB\)\]](#) [CNF](#)

41 Ion implantation issues in microelectronic device manufacturing

Bala, K.; Hoepfner, J.; El-Kareh, B.

Electronic Components and Technology Conference, 1995. Proceedings., 45th

Page(s): 51 -57

[\[Abstract\]](#) [\[PDF Full-Text \(660 KB\)\]](#) [CNF](#)

42 Influence of tilted high-energy ion-implantation upon scaled CMOS device structure

Takatsuka, H.; Sato, H.; Izawa, T.; Hisaeda, T.; Goto, H.; Kawamura, S.

Microelectronic Test Structures, 1995. ICMTS 1995. Proceedings of the 1995 International Conference on, 1995

Page(s): 247 -251

[\[Abstract\]](#) [\[PDF Full-Text \(476 KB\)\]](#) [CNF](#)

43 A zinc calcium phosphorous oxide ceramic and malic acid-Ca(OH)₂-vitamin E composite for repairing bone defects

Longo, A.; Mehling, B.; Barre, P.; Snead, D.; Taylor, A.; Reynolds, D.; Bajpai, A.

Biomedical Engineering Conference, 1995., Proceedings of the 1995 Fourteenth Southern, 1995

Page(s): 117 -120

[\[Abstract\]](#) [\[PDF Full-Text \(444 KB\)\]](#) [CNF](#)

44 Optimization of boron pocket implantation for deep sub-micron NMOS process

Chun Jiang; Nowak, E.; Ding, L.; Loh, Y.T.

Solid-State and Integrated Circuit Technology, 1995 4th International Conference, 1995

Page(s): 224 -226

[\[Abstract\]](#) [\[PDF Full-Text \(172 KB\)\]](#) **CNF**

**45 A scaled 1.8 V, 0.18 μm gate length CMOS technology: dev
design and reliability considerations**

Rodder, M.; Aur, S.; Chen, I.-C.

Electron Devices Meeting, 1995., International , 1995

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46 **Implanted doping profile engineering design for manufacturability**
Kau, D.C.; Steeples, K.; Andreoli, M.; Podbevsek, A.; Tower, B.; Bouchard, I
Advanced Semiconductor Manufacturing Conference and Workshop. 1994 IE
1994

Page(s): 37

[\[Abstract\]](#) [\[PDF Full-Text \(32 KB\)\]](#) **CNF**

47 **A study of design/process dependence of 0.25 /spl mu/m gate lei**
CMOS

Rodder, M.; Amerasekera, A.; Aur, S.; Chen, I.C.

Electron Devices Meeting, 1994. Technical Digest., International , 1994

Page(s): 71 -74

[\[Abstract\]](#) [\[PDF Full-Text \(332 KB\)\]](#) **CNF**

48 **SOI LIGBT devices with a dual P-well implant for improved latchin**
characteristics

*Disney, D.R.; Plummer, J.D.*Power Semiconductor Devices and ICs, 1993. ISPSD '93., Proceedings of the
International Symposium on , 1993

Page(s): 254 -258

[\[Abstract\]](#) [\[PDF Full-Text \(440 KB\)\]](#) **CNF**

49 **Soft-error study of DRAMs using nuclear microprobe**

Ohno, Y.; Kimura, H.; Sonoda, K.; Satoh, S.; Sayama, H.; Hara, S.; Takai, I
Miyoshi, H.

Reliability Physics Symposium, 1993. 31st Annual Proceedings., Internationa

Page(s): 150 -155

[\[Abstract\]](#) [\[PDF Full-Text \(444 KB\)\]](#) **CNF**

50 Performance evaluation of CMOS compatible bipolar transistors at vertical junction FETs for advanced VLSI technology

Nouailhat, A.; Mouis, M.; Marty, A.; Granier, A.; Degors, N.; Kirtsch, J.; Cha
Electronics Letters, Volume: 28 Issue: 23, 5 Nov. 1992

Page(s): 2195 -2196

[\[Abstract\]](#) [\[PDF Full-Text \(160 KB\)\]](#) **JNL**

51 A 34-ns 16-Mb DRAM with controllable voltage down-converter

Hidaka, H.; Arimoto, K.; Hirayama, K.; Hayashikoshi, M.; Asakura, M.; Tsuk. Oishi, T.; Kawai, S.; Suma, K.; Konishi, Y.; Tanaka, K.; Wakamiya, W.; Ohn Fujishima, K.

Solid-State Circuits, IEEE Journal of, Volume: 27 Issue: 7, July 1992

Page(s): 1020 -1027

[\[Abstract\]](#) [\[PDF Full-Text \(920 KB\)\]](#) **JNL**

52, A PC-based real-time simulator of cardiac bradycardia and tachyc: arrhythmias

Steinhaus, B.M.; Wells, R.T.; Hursta, W.N.

Computers in Cardiology 1992, Proceedings of, 1992

Page(s): 587 -590

[\[Abstract\]](#) [\[PDF Full-Text \(220 KB\)\]](#) **CNF**

53 A high performance 0.6 μ m BiCMOS SRAM technology with emil self-aligned bipolar transistors and retrograde well for MOS transistors

Honda, H.; Uga, K.; Ishida, M.; Ishigaki, Y.; Takahashi, J.; Shiomi, T.; Ohba Kohno, Y.

VLSI Technology, 1992. Digest of Technical Papers. 1992 Symposium on, 1992

Page(s): 34 -35

[\[Abstract\]](#) [\[PDF Full-Text \(160 KB\)\]](#) **CNF**

54 The vertical IGBT with an implanted buried layer

Eranen, S.; Blomberg, M.

Power Semiconductor Devices and ICs, 1991. ISPSD '91., Proceedings of the International Symposium on, 1991

Page(s): 211 -214

[\[Abstract\]](#) [\[PDF Full-Text \(284 KB\)\]](#) **CNF**

55 A self-aligned retrograde twin-well structure with buried p/sup +
Odanaka, S.; Yabu, T.; Shimizu, N.; Umimoto, H.; Ohzone, T.
Electron Devices, IEEE Transactions on , Volume: 37 Issue: 7 , July 1990
Page(s): 1735 -1742

[\[Abstract\]](#) [\[PDF Full-Text \(644 KB\)\]](#) **JNL**

**56 Strongly asymmetric doping profiles at mask edges in high-energy
implantation**
Wijburg, R.C.; Hemink, G.J.; Middelhoek, J.
Electron Devices, IEEE Transactions on , Volume: 37 Issue: 1 , Jan. 1990
Page(s): 79 -87

[\[Abstract\]](#) [\[PDF Full-Text \(864 KB\)\]](#) **JNL**

**57 30 GHz polysilicon-emitter and single-crystal-emitter graded SiGe
PNP transistors**
*Harambe, D.L.; Stork, J.M.C.; Meyerson, B.S.; Crabbe, E.F.; Scilla, G.J.; de F.
Megdanis, A.E.; Stanis, C.L.; Patton, G.L.; Comfort, J.H.; Bright, A.A.; Johns
Furkay, S.S.*
Electron Devices Meeting, 1990. Technical Digest., International , 1990
Page(s): 33 -36

[\[Abstract\]](#) [\[PDF Full-Text \(328 KB\)\]](#) **CNF**

58 A self-aligned retrograde twin-well structure with buried p/sup +
Odanaka, S.; Yabu, T.; Shimizu, N.; Umimoto, H.; Ohzone, T.
IEEE Electron Device Letters , Volume: 10 Issue: 6 , June 1989
Page(s): 280 -282

[\[Abstract\]](#) [\[PDF Full-Text \(220 KB\)\]](#) **JNL**

59 Anomalous punchthrough in ULSI buried-channel MOSFETs
Skotnicki, T.; Merckel, G.; Pedron, T.
Electron Devices, IEEE Transactions on , Volume: 36 Issue: 11 Part: 2 , Nov.
Page(s): 2548 -2556

[\[Abstract\]](#) [\[PDF Full-Text \(648 KB\)\]](#) **JNL**

60 Tachyarrhythmia detection by implantable defibrillator

Kongyan, P.; Thakor, N.V.

Engineering in Medicine and Biology Society, 1989. Images of the Twenty-Fi
Century., Proceedings of the Annual International Conference of the IEEE En
in , 1989

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VLSI Technology, Systems and Applications, 1989. Proceedings of Technical 1989 International Symposium on , 1989

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